

2N6517

High Voltage Transistor

- Collector-Emitter Voltage: V_{CEO}=350V
 Collector Dissipation: P_C (max)=625mW
 Complement to 2N6520

- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	350	V
V _{CEO}	Collector-Emitter Voltage	350	V
V_{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	500	mA
P _C	Collector Power Dissipation	625	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Refer to 2N6515 for graphs

Electrical Characteristics T_a=25°C unless otherwise noted

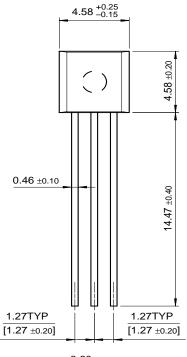
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	* Collector-Emitter Breakdown Voltage	I _C =1mA, I _B =0	350			V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	350			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E=10\mu A, I_C=0$	6			V
I _{CBO}	Collector Cut-off Current	V_{CB} =250V, I_{E} =0			50	nA
I _{EBO}	Emitter Cut-off Current	V_{EB} =5V, I_{C} =0			50	nA
h _{FE}	* DC Current Gain	I _C =1mA, V _{CE} =10V I _C =10mA, V _{CE} =10V I _C =30mA, V _{CE} =10V I _C =50mA, V _{CE} =10V I _C =100mA, V _{CE} =10V	20 30 30 20 15		200 200	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I_{C} =10mA, I_{B} =1mA I_{C} =20mA, I_{B} =2mA I_{C} =30mA, I_{B} =3mA I_{C} =50mA, I_{B} =5mA			0.3 0.35 0.5 1	V V V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I_C =10mA, I_B =1mA I_C =20mA, I_B =2mA I_C =30mA, I_B =3mA			0.75 0.85 0.9	V V V
C _{ob}	Output Capacitance	V _{CB} =20V, I _E =0, f=1MHz			6	pF
f _T	* Current Gain Bandwidth Product	I _C =10mA, V _{CE} =20V, 40 20 f=20MHz		200	MHz	
V _{BE} (on)	Base Emitter On Voltage	I _C =100mA, V _{CE} =10V			2	V

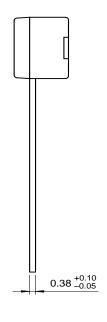
* Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

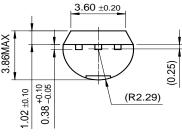
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Package Dimensions

TO-92







Dimensions in Millimeters

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